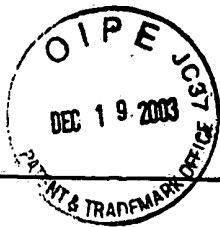


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<b>FORM PTO - 1449</b>				<b>ATTORNEY DOCKET NO.: ASC-022CPC1</b>			
<b>INFORMATION DISCLOSURE STATEMENT</b>				<b>APPLICANT(S): Wu et al.</b>			
				<b>SERIAL NO.: 10/603,852</b>			
				<b>FILING DATE: June 25, 2003</b>		<b>GROUP: 2811</b>	
<b>U.S. PATENT DOCUMENTS</b>							
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210	A1	4,010,045	03/01/1977	Ruehrwein			
	A2	5,013,681	05/07/1991	Godbey et al.			
	A3	5,166,084	11/24/1992	Pfiester			
	A4	5,202,284	04/13/1993	Kamins et al.			
	A5	5,207,864	05/04/1993	Bhat et al.			
	A6	5,208,182	05/04/1993	Narayan et al.			
	A7	5,212,110	05/18/1993	Pfiester et al.			
	A8	5,221,413	06/22/1993	Brasen et al.			
	A9	5,285,086	02/08/1994	Fitzgerald			
	A10	5,310,451	05/10/1994	Tejwani et al.			
	A11	5,346,848	09/13/1994	Gruppen-Shemansky et al.			
	A12	5,374,564	12/20/1994	Bruel			
	A13	5,413,679	05/09/1995	Godbey			
	A14	5,442,205	08/15/1995	Brasen et al.			
	A15	5,461,243	10/24/1995	Ek et al.			
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	A17	5,476,813	12/19/1995	Naruse			
	A18	5,484,664	01/16/1996	Kitahara et al.			
	A19	5,523,592	06/04/1996	Nakagawa et al.			
	A20	5,534,713	07/09/1996	Ismail et al.			
	A21	5,536,361	07/16/1996	Kondo et al.			
	A22	5,540,785	07/30/1996	Dennard et al.			
	A23	5,683,934	11/04/1997	Candelaria			
210	A24	5,728,623	03/17/1998	Mori			
<b>EXAMINER</b> <i>Doug L. O.</i>				<b>DATE CONSIDERED</b> <i>5/21/04</i>			



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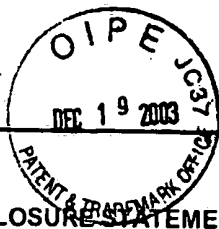
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OK	A25	5,759,898	06/02/1998	Ek et al.			
	A26	5,792,679	08/11/1998	Nakato			
	A27	5,877,070	03/02/1999	Goesele et al.			
	A28	5,891,769	04/06/1999	Liaw et al.			
	A29	5,906,708	05/25/1999	Robinson et al.			
	A30	5,906,951	05/25/1999	Chu et al.			
	A31	5,943,560	08/24/1999	Chang et al.			
	A32	5,966,622	10/12/1999	Levine et al.			
	A33	5,998,807	12/07/1999	Lustig et al.			
	A34	6,033,974	03/07/2000	Henley et al.			
	A35	6,033,995	03/07/2000	Muller			
	A36	6,059,895	05/09/2000	Chu et al.			
	A37	6,074,919	06/13/2000	Gardner et al.			
	A38	6,096,590	08/01/2000	Chan et al.			
	A39	6,103,559	08/15/2000	Gardner et al.			
	A40	6,107,653	08/22/2000	Fitzgerald			
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	A42	6,117,750	09/12/2000	Bensahel et al.			
	A43	6,153,495	11/28/2000	Kub et al.			
	A44	6,154,475	11/28/2000	Soref et al.			
	A45	6,162,688	12/19/2000	Gardner et al.			
	A46	6,184,111 B1	02/06/2001	Henley et al.			
	A47	6,191,007 B1	02/20/2001	Matsui et al.			
	A48	6,191,432 B1	02/20/2001	Sugiyama et al.			
OK	A49	6,194,722 B1	02/27/2001	Howe et al.			
EXAMINER <i>Dan H. Owen</i>				DATE CONSIDERED <i>5/21/04</i>			



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	A51	6,210,988 B1	04/03/2001	Howe et al.			
	A52	6,218,677 B1	04/17/2001	Broekaert			
	A53	6,232,138 B1	05/15/2001	Fitzgerald et al.			
	A54	6,235,567 B1	05/22/2001	Huang			
	A55	6,251,755 B1	06/26/2001	Furukawa et al.			
	A56	6,261,929 B1	07/17/2001	Gehrke et al.			
	A57	6,291,321 B1	09/18/2001	Fitzgerald			
	A58	6,313,016 B1	11/06/2001	Kibbel et al.			
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	A61	6,350,993 B1	02/26/2002	Chu et al.			
	A62	6,368,733 B1	04/09/2002	Nishinaga			
	A63	6,372,356 B1	04/16/2002	Thornton et al.			
	A65	6,573,126	06/03/2003	Cheng et al.			
	A66	6,583,015	06/24/2003	Fitzgerald et al.			
	A67	2001/0003269 A1	06/14/2001	Wu et al.			
	A68	2002/0125497	09/12/2002	Fitzgerald			
OKO	A69	2003/0013323	01/16/2003	Hammond et al.			

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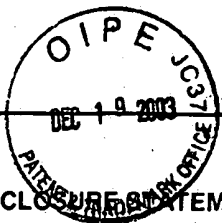
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OKO	B2	0 683 522 A2	11/22/1995	EP				No	Yes

EXAMINER

*Douglas H. Owen*

DATE CONSIDERED

5/21/04



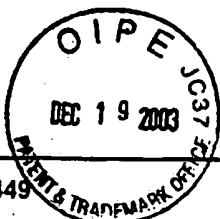
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Qho	B3	0 828 296	03/11/1998	EP			No	Yes	
Qho	B4	2000-31491	01/28/2000	JP			No	Yes	
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Qho	B6	WO 99/53539	10/21/1999	PCT			No	Yes	
Qho	B7	WO 00/48239	08/17/2000	PCT			No	Yes	
Qho	B8	WO 01/99169	12/27/2001	PCT			No	Yes	
OTHER ART, JOURNAL ARTICLES, ETC.									
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)								
Qho	C1	Armstrong, "Technology for SiGe Heterostructure-Based CMOS Devices," Thesis Submitted to the Massachusetts Institute of Technology Department of Electrical Engineering and Computer Science on June 30, 1999, pp. 1-154.							
Qho	C2	Barradas et al., "RBS analysis of MBE-grown SiGe/(001) Si heterostructures with thin, high Ge content SiGe channels for HMOS transistors," <u>Modern Physics Letters B</u> , (2001), abstract.							
Qho	C3	Borenstein et al., "A New Ultra-Hard Etch-Stop Layer for High Precision Micromachining," <u>Proceedings of the 1999 12<sup>th</sup> IEEE International Conference on Micro Electro Mechanical Systems (MEMS)</u> , January 17-21, 1999, pps. 205-210.							
Qho	C4	Bruehl et al., "SMART CUT: A Promising New SOI Material Technology," <u>Proceedings of the 1995 IEEE International SOI Conference</u> (October 1995), pp. 178-179.							
Qho	C5	Bruehl, "Silicon on Insulator Material Technology," <u>Electronic Letters</u> , Vol. 13, No. 14 (July 6, 1995), pp. 1201-1202.							
Qho	C6	Brunner et al., "Molecular beam epitaxy growth and thermal stability of Si <sub>1-x</sub> Ge <sub>x</sub> layers on extremely thin silicon-on-insulator substrates," <u>Thin Solid Films</u> , Vol. 321 (1998), pp. 245-250.							
Qho	C7	Chang et al., "Selective Etching of SiGe/Si Heterostructures," <u>Journal of the Electrochemical Society</u> , No. 1 (January 1991), pp. 202-204.							
Qho	C8	Chen et al., "The Band Model and the Etching Mechanism of Silicon in Aqueous KOH," <u>Journal of the Electrochemical Society</u> , Vol. 142, No. 1 (January 1995), pp. 170-176.							
EXAMINER <i>W. H. Owe</i>					DATE CONSIDERED 5/22/04				



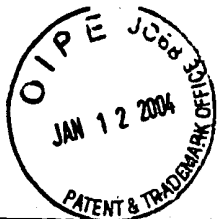
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OTHER ART, JOURNAL ARTICLES, ETC.			
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)		
Wro	C9	Cheng et al., "Electron Mobility Enhancement in Strained-Si n-MOSFETs Fabricated on SiGe-on-Insulator (SGOI) Substrates," <u>IEEE Electron Device Letters</u> , Vol. 22, No. 7 (July 2001), pp. 321-323.	
	C10	Cheng et al., "Relaxed Silicon-Germanium on Insulator Substrate by Layer Transfer," <u>Journal of Electronic Materials</u> , Vol. 30, No. 12 (2001), pp. L37-L39.	
	C11	Feijoo et al., "Epitaxial Si-Ge Etch Stop Layers with Ethylene Diamine Pyrocatechol for Bonded and Etchback Silicon-on-Insulator," <u>Journal of Electronic Materials</u> , Vol. 23, No. 6 (June 1994), pps. 493-496.	
	C12	Finne et al., "A Water-Amine-Complexing Agent System for Etching Silicon," <u>Journal of the Electrochemical Society</u> , Vol. 114, No. 9 (September 1967), pp. 965-970.	
	C13	Fitzgerald et al., "Relaxed $GexSi_{1-x}$ structures for III-V integration with Si and high mobility two-dimensional electron gases in Si," <u>Journal of Vacuum Science and Technology B</u> , Vol. 10, No. 4 (July/August 1992), pp. 1807-1819.	
	C14	Fitzgerald et al., "Totally Relaxed $GexSi_{1-x}$ Layers with Low Threading Dislocation Densities Grown on Si Substrates," <u>Applied Physics Letters</u> , Vol. 59, No. 7 (August 12, 1991), pps. 811-813.	
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	C16	Godbey et al., "A $Si_{0.7}Ge_{0.3}$ strained-layer etch stop for the generation of thin layer undoped silicon," <u>Applied Physics Letters</u> , Vol. 56, No. 4 (January 22, 1990), pp. 373-375.	
	C17	Hackbarth et al., "Alternatives to thick MBE-grown relaxed SiGe buffers," <u>Thin Solid Films</u> , Vol. 369, No. 1-2 (July 2000), pp. 148-151.	
	C18	Huang et al., "High-quality strain-relaxed SiGe alloy grown on implanted silicon-on-insulator substrate," <u>Applied Physics Letters</u> , Vol. 76, No. 19 (May 8, 2000), pp. 2680-2682.	
	C19	Ishikawa et al., "Creation of Si-Ge-based SIMOX structures by low energy oxygen implantation," <u>Proceedings of the 1997 IEEE International SOI Conference</u> (October 1997), pp. 16-17.	
	C20	Ishikawa et al., "SiGe-on-insulator substrate using SiGe alloy grown Si(001)," <u>Applied Physics Letters</u> , Vol. 75, No. 7 (August 16, 1999), pp. 983-985.	
	C21	Ismail, "Si/SiGe High-Speed Field-Effect Transistors," Electron Devices Meeting, Washington D.C., December 10, 1995.	
	C22	König et al., "Design Rules for n-Type SiGe Hetero FETs," <u>Solid State Electronics</u> , Vol. 41, No. 10 (1997), pp. 1541-1547.	
Wro	C23	Leancu et al., "Anisotropic etching of germanium," <u>Sensors and Actuators A</u> , Vol. 46-47 (1995), pp. 35-37.	
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Wong L. O.		5/22/04	



FORM PTO - 1449		ATTORNEY DOCKET NO.: ASC-022CPC1	
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OTHER ART, JOURNAL ARTICLES, ETC.			
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)		
QW	C24	LeGoues et al., "Relaxation of SiGe thin films grown on Si/SiO <sub>2</sub> substrates," <u>Applied Physics Letters</u> , Vol. 75, No. 11 (June 1, 1994), pp. 7240-7246.	
	C25	Leitz et al., "Dislocation glide and blocking kinetics in compositionally graded SiGe/Si," <u>Journal of Applied Physics</u> , Vol. 90, No. 6 (September 15, 2001), pp. 2730-2736.	
	C26	Maiti et al., "Strained-Si heterostructure field effect transistors," <u>Semiconductor Science and Technology</u> , Vol. 13 (1998), pp. 1225-1246.	
	C27	Mazara, "Silicon-On-Insulator by Wafer Bonding: A Review," <u>Journal of the Electrochemical Society</u> , No. 1 (January 1991), pp. 341-347.	
	C28	Mizuno et al., "Electron and Hole Mobility Enhancement in Strained-Si MOSFET's on SiGe-on-Insulator Substrates Fabricated by SIMOX Technology," <u>IEEE Electron Device Letters</u> , Vol. 21, No. 5 (May 2000), pp. 230-232.	
	C29	Narozny et al., "Si/SiGe Heterojunction Bipolar Transistor with Graded GAP SiGe Base Made by Molecular Beam Epitaxy," <u>IEEE IEDM</u> (1988), pp. 562-565.	
	C30	Powell et al., "New approach to the growth of low dislocation relaxed SiGe material," <u>Applied Physics Letters</u> , Vol. 64, No. 14 (April 4, 1994), pp. 1865-1858.	
	C31	Rim et al., "Fabrication and Analysis of Deep Submicron Strained-Si N-MOSFET's," <u>IEEE Transactions on Electron Devices</u> , Vol. 47, No. 7 (July 2000), pp. 1406-1415.	
	C32	Sadek et al., "Design of Si/SiGe Heterojunction Complementary Metal-Oxide-Semiconductor Transistors," <u>IEEE Trans. Electron Devices</u> , Vol. 43, No. 8 (August 1996), pp. 1224-1232.	
	C33	Seidel et al., "Anisotropic Etching of Crystalline Silicon in Alkaline Solutions," <u>Journal of the Electrochemical Society</u> , Vol. 137, No. 11 (November 1990), pp. 3626-3632.	
	C34	Shang et al., "The Development of an Anisotropic Si Etch Process Selective to Ge <sub>x</sub> Si <sub>1-x</sub> Underlayers," <u>Journal of the Electrochemical Society</u> , Vol. 141, No. 2 (February 1994), pp. 507-510.	
	C35	Takagi et al., "On the Universality of Inversion Layer Mobility in Si MOSFET's: Part I-Effects of Substrate Impurity Concentration," <u>IEEE Transactions on Electron Devices</u> , Vol. 41, No. 12 (December 1994), pp. 2357-2362.	
	C36	Ting et al., "Monolithic Integration of III-V Materials and Devices on Silicon," Part of the SPIE Conference on Silicon-Based Optoelectronics, San Jose, CA, (January 1999), pp. 19-28.	
	C37	Usami et al., "Spectroscopic study of Si-based quantum wells with neighboring confinement structure," <u>Semiconductor Science and Technology</u> , (1997), abstract.	
OK	C38	Wu, "Novel Etch-Stop Materials for Silicon Micromachining," Thesis Submitted to the Massachusetts Institute of Technology Department of Materials Science and Engineering on May 9, 1997, pp. 1-62.	
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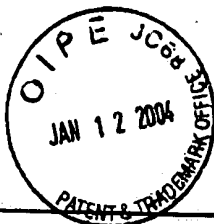


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OTHER ART, JOURNAL ARTICLES, ETC.			
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)		
OK	C39	Yeo et al., "Nanoscale Ultra-Thin-Body Silicon-on-Insulator P-MOSFET with a SiGe/Si Heterostructure Channel," <u>IEEE Electron Device Letters</u> , Vol. 21, No. 4 (April 2000), pp. 161-163.	
I	C40	Yi et al., "Si <sub>1-x</sub> Ge <sub>x</sub> /Si Multiple Quantum Well Wires Fabricated Using Selective Etching," <u>Materials Research Society Symposium Proceedings</u> , Vol. 379 (1995), pp. 91-96.	
I	C41	Zhang et al., "Demonstration of a GaAs-Based Compliant Substrate Using Wafer Bonding and Substrate Removal Techniques," <u>Electronic Materials and Processing Research Laboratory, Department of Electrical Engineering, University Park, PA 16802</u> , (1998), pp. 25-28.	
OK	C42	IBM Technical Disclosure Bulletin, Vol. 32, No. 8A, January 1990, "Optimal Growth Technique and Structure for Strain Relaxation of Si-Ge Layers on Si Substrates," pp. 330-331.	
EXAMINER <i>W. H. O.</i>		DATE CONSIDERED 5/22/04	



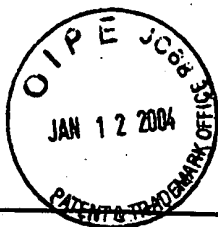
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OTHER ART, JOURNAL ARTICLES, ETC.									
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)								
DWC	C43	Batterman, "Hillocks, Pits, and Etch Rate in Germanium Crystals," <u>Journal of Applied Physics</u> , Vol. 28, No. 11 (November, 1957), pp. 1236-1241.							
	C44	Bohg, "Ethylene Diamine-Pyrocatechol-Water Mixture Shows Etching Anomaly in Boron-Doped Silicon," <u>Journal of the Electrochemical Society</u> , Vol. 118, No. 2 (February 1971), pp. 401-402.							
	C45	Desmond <i>et al.</i> , "The Effects of Process-Induced Defects on the Chemical Selectivity of Highly Doped Boron Etch Stops in Silicon," <u>Journal of the Electrochemical Society</u> , Vol. 141, No. 1 (January 1994), pp. 178-184.							
	C46	Ehman <i>et al.</i> , "Morphology of Etch Pits on Germanium Studied by Optical and Scanning Electron Microscopy," <u>Journal of Applied Physics</u> , Vol. 41, No. 7 (June 1970), pp. 2824-2827.							
	C47	Feijóo <i>et al.</i> , "Etch Stop Barriers in Silicon Produced by Ion Implantation of Electrically Non-Active Species," <u>Journal of the Electrochemical Society</u> , Vol. 139, No. 8 (August 1992), pp. 2309-2313.							
	C48	Fitzgerald, "GeSi/Si Nanostructures," <u>Annual Review of Materials Science</u> , Vol. 25 (1995), pp. 417-454.							
DWC	C49	Frank, "Orientation-Dependent Dissolution of Germanium," <u>Journal of Applied Physics</u> , Vol. 31, No. 11 (November 1960), pp. 1996-1999.							
EXAMINER <i>Douglas H. Jones</i>				DATE CONSIDERED <i>5/22/04</i>					





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FORM PTO - 1449		ATTORNEY DOCKET NO.: ASC-022CPC1	
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EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)		
249	C50	Ghandi <i>et al.</i> , "Chemical Etching of Germanium," <u>Journal of the Electrochemical Society</u> , Vol. 135, No. 8 (August 1988), pp.2053-2054.	
	C51	Herzog <i>et al.</i> , "X-Ray Investigation of Boron- and Germanium-Doped Silicon Epitaxial Layers," <u>Journal of the Electrochemical Society</u> , Vol. 131, No. 12 (December 1984), pp.2969-2974.	
	C52	Holmes, "The Orientation Dependence of Etching Effects on Germanium Crystals," <u>Acta Metallurgica</u> , Vol. 7, No. 4 (April 1959), pp. 283-290.	
	C53	Hunt <i>et al.</i> , "Selective Etch Stop by Stress Compensation for Thin-Film BESOI," <u>1990 IEEE/SOI Technology Conference</u> , (October 2-4, 1990), pp.145-146.	
	C54	Jaccodine, "Use of Modified Free Energy Theorems to Predict Equilibrium Growing and Etching Shapes," <u>Journal of Applied Physics</u> , Vol. 33, No. 8 (August 1962), pp. 2643-2647.	
	C55	Kern, "Chemical Etching of Silicon, Germanium, Gallium, Arsenide, and Gallium Phosphide," <u>RCA Review</u> , Vol. 39 (June 1978), pp. 278-308.	
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	C57	Leancu <i>et al.</i> , "Anisotropic Etching of Germanium," <u>Sensors and Actuators</u> , A46-47 (1995), pp. 35-37.	
	C58	Lehmann <i>et al.</i> , "Implanted Carbon: An Effective Etch-Stop in Silicon," <u>Journal of the Electrochemical Society</u> , Vol. 138, No.5 (May 1991), pp. 3-4.	
	C59	Palik <i>et al.</i> , "Ellipsometric Study of the Etch-Stop Mechanism in Heavily Doped Silicon," <u>Journal of the Electrochemical Society</u> , Vol. 132, No. 1 (January 1985), pp. 135-141.	
	C60	Palik <i>et al.</i> , "Study of Bias-Dependent Etching of Si in Aqueous KOH," <u>Journal of the Electrochemical Society</u> , Vol. 134, No. 2 (February 1987), pp. 404-409.	
	C61	Palik <i>et al.</i> , "Study of the Etch-Stop Mechanism in Silicon," <u>Journal of the Electrochemical Society</u> , Vol. 129, No. 9 (September 1982), pp.2051-2059.	
	C62	Petersen <i>et al.</i> , "Silicon as a Mechanical Material," <u>Proceedings of the IEEE</u> , Vol. 70, No. 5 (May 1982), pp. 420-457.	
240	C63	Rai-Choudhury <i>et al.</i> , "Doping of Epitaxial Silicon," <u>Journal of Crystal Growth</u> , Vol. 7 (1970), pp. 361-367.	
EXAMINER		DATE CONSIDERED	
Douglas K. [Signature]		5/22/04	



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OTHER ART, JOURNAL ARTICLES, ETC.			
EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)		
OKO	C64	Raley <i>et al.</i> , "(100) Silicon Etch-Rate Dependence on Boron Concentration in Ethylenediamine-Pyrocatechol-Water Solutions," <u>Journal of the Electrochemical Society</u> , Vol. 131, No. 1 (January 1984), pp. 161-170.	
	C65	Senna <i>et al.</i> , "Gallium Doping for Silicon Etch Stop in KOH," <u>Transducers '95/Euroensors IX</u> , the 8 <sup>th</sup> International Conference on Solid-State Sensors and Actuators and Euroensors IX, Stockholm, Sweden, June 25-29, 1995, pp. 194-195.	
	C66	Soderberg, "Fabrication of BESOI Materials Using Implanted Nitrogen as an Effective Etch Stop Barrier," <u>1989 IEEE SOS/SOI Technology Conference</u> , (October 3-5, 1989), pp. 64.	
	C67	Sundaram <i>et al.</i> , "Electrochemical etching of Silicon by Hydrazine," <u>Journal of the Electrochemical Society</u> , Vol. 140, No. 6 (June 1993), pp. 1592-1597.	
	C68	Sze, "Physics of Semiconductor Devices," (1991).	
OKO	C69	Vol'fson <i>et al.</i> , "Fundamental Absorption Edge of Silicon Heavily Doped with Donor or Acceptor Impurities," <u>Soviet Physics Semiconductors</u> , Vol. 1, No. 3 (September 1967), pp. 327-332.	
EXAMINER	Dough M. Qua		DATE CONSIDERED 5/22/04

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